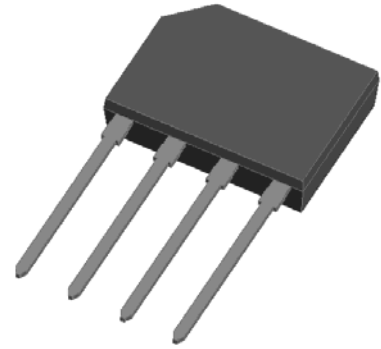


## Features

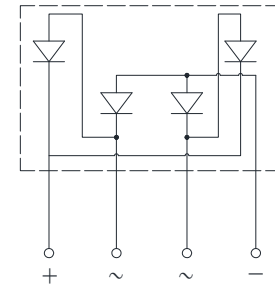
- Glass passivated chip junction
- Ideal for printed circuit boards
- High surge current capability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

RoHS  
COMPLIANT



## Typical Applications

General purpose use in AC/DC bridge full wave rectification for monitor, TV, printer, power supply, switching mode power supply, adapter, audio equipment, and home appliances applications.



## Mechanical Data

- **Package:** GBP  
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked on body

## ■ Maximum Ratings ( $T_a=25^{\circ}\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GBP8005	GBP801	GBP802	GBP804	GBP806	GBP808	GBP810
Device marking code			GBP8005	GBP801	GBP802	GBP804	GBP806	GBP808	GBP810
Maximum Repetitive Peak Reverse Voltage	VRRM	V	50	100	200	400	600	800	1000
Maximum RMS Voltage	VRMS	V	35	70	140	280	420	560	700
Maximum DC blocking Voltage	VDC	V	50	100	200	400	600	800	1000
Average rectified output current @60Hz sine wave, R-load	With heatsink $T_c = 130^{\circ}\text{C}$	IO	A	8.0					
	Without heatsink $T_a = 25^{\circ}\text{C}$			1.8					
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, $T_j=25^{\circ}\text{C}$	IFSM	A	170						
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, $T_j=25^{\circ}\text{C}$			340						
Current squared time @1ms≤t<8.3ms $T_j=25^{\circ}\text{C}$ , Rating of per diode	I <sup>2</sup> t	A <sup>2</sup> s	120						
Dielectric strength @ terminals to case, AC 1 minute	Vdis	KV	2						
Storage temperature	T <sub>stg</sub>	°C	-55 ~ +150						
Junction temperature	T <sub>j</sub>	°C	-55 ~ +150						

### ■ Electrical Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	GBP8005	GBP801	GBP802	GBP804	GBP806	GBP808	GBP810
Maximum instantaneous forward voltage drop per diode	V <sub>F</sub>	V	I <sub>FM</sub> =4.0A	1.0						
Maximum DC reverse current at rated DC blocking voltage per diode	I <sub>R</sub>	μA	T <sub>j</sub> =25°C	5						
			T <sub>j</sub> =125°C	100						
Typical junction capacitance	C <sub>j</sub>	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	48						

### ■ Thermal Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GBP8005	GBP801	GBP802	GBP804	GBP806	GBP808	GBP810
Thermal Resistance	Between junction and ambient, Without heatsink	R <sub>θJ-A</sub>	°C/W	45.0					
	Between junction and case, With heatsink	R <sub>θJ-C</sub>		1.5					

Note: Device mounted on 75mm x 45mm x 5.5mm Aluminum Plate Heatsink.

### ■ Characteristics (Typical)

FIG1: I<sub>o</sub>-T<sub>c</sub> Curve

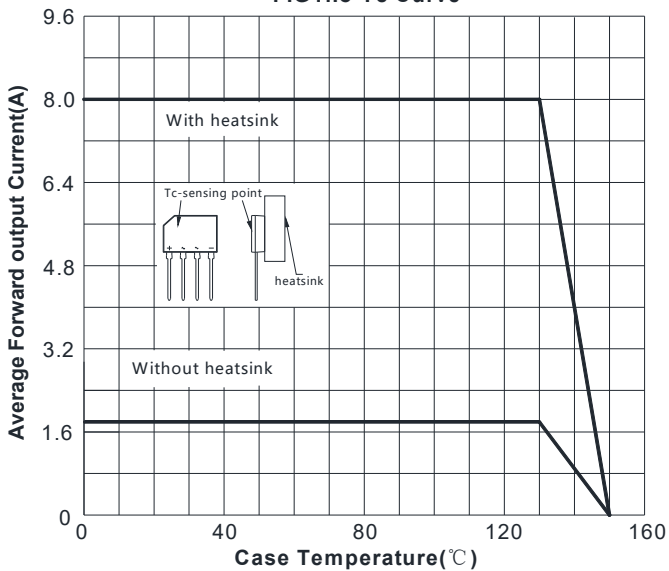


FIG2: Surge Forward Current Capability

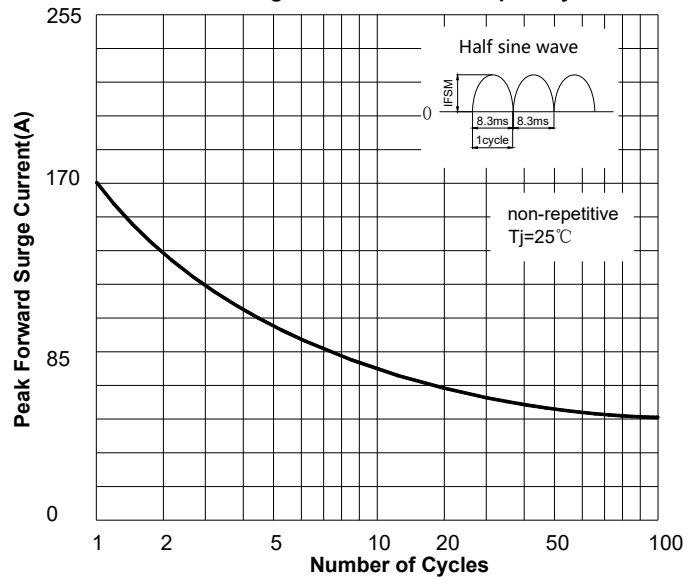


FIG3: Typical Forward Voltage

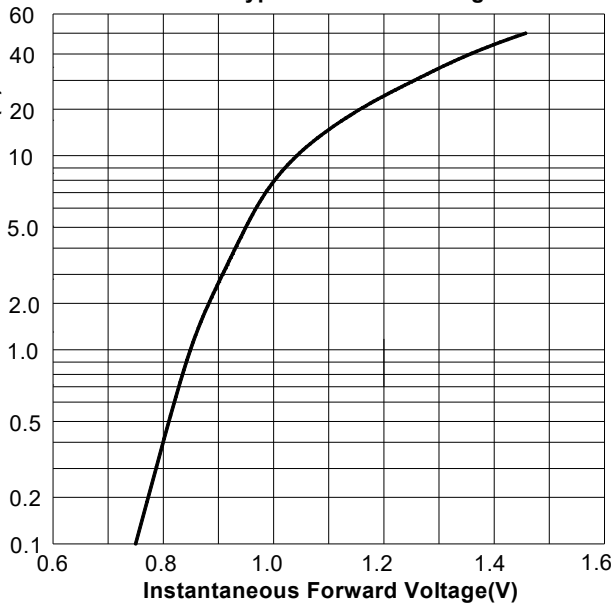
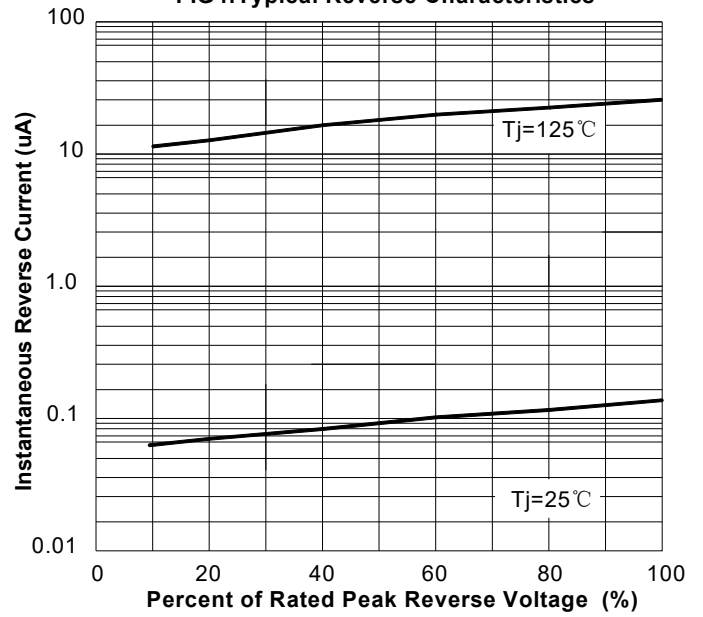
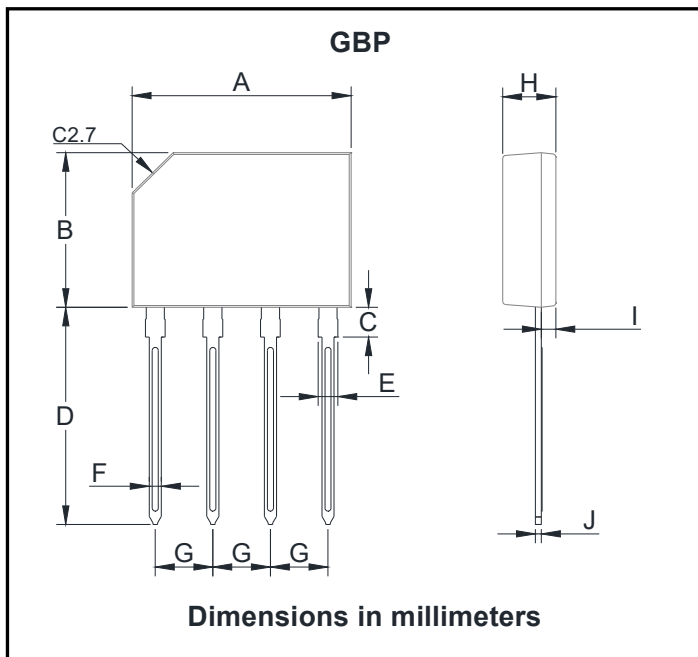


FIG4: Typical Reverse Characteristics



## ■ Outline Dimensions



GBP		
Dim	Min	Max
A	14.25	14.75
B	10.10	10.60
C	1.80	2.20
D	14.25	14.73
E	1.22	1.42
F	0.76	0.86
G	3.70	3.90
H	3.35	3.65
I	0.80	1.10
J	0.35	0.55